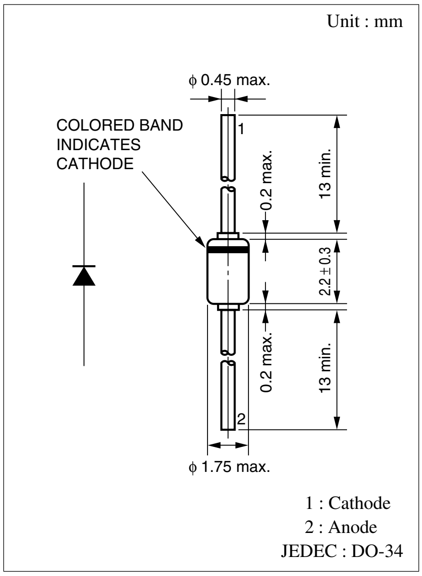
MA2C856

Silicon epitaxial planar type

For band switching



■ Features

- Extra-small DHD envelope, allowing to insert into a 5 mm pitch hole
- Less voltage dependence of the terminal capacitance C_t
- Low forward dynamic resistance r_f
- Optimum for a band switching of a tuner

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature	T_{opr}	−25 to +85	°C
Storage temperature	T_{stg}	−55 to +100	°C

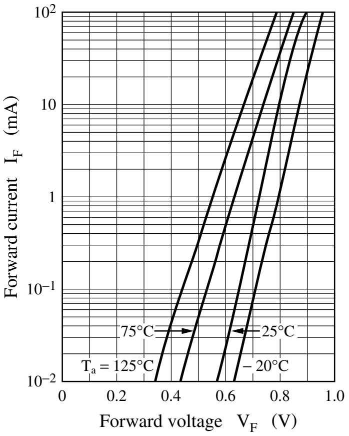
■ Electrical Characteristics $T_a = 25°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)*	I_R	$V_R = 33$ V			100	nA
Forward voltage (DC)	V_F	$I_F = 100$ mA			1	V
Terminal capacitance	C_t	$V_R = 15$ V, f = 1 MHz			2	pF
Forward dynamic resistance	r_f	$I_F = 3$ mA, f = 100 MHz			0.85	Ω

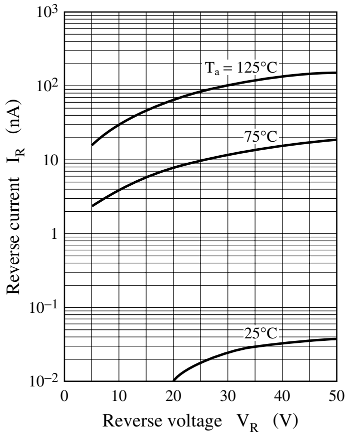
Note) 1. Rated input/output frequency: 100 MHz
2. * : Measurement with the beam shielded

■ Cathode Indication

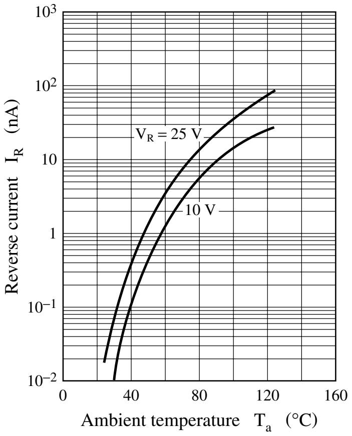
Type No.	MA2C856
Color	Yellow



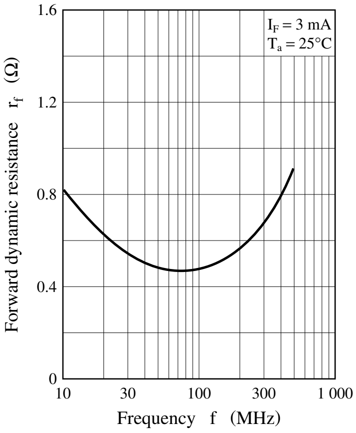
I_F — V_F



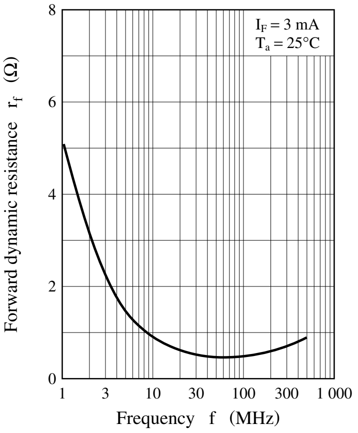
I_R — V_R



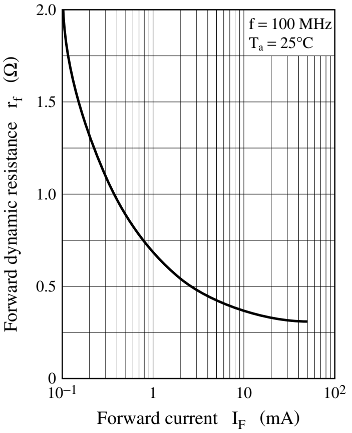
I_R — T_a



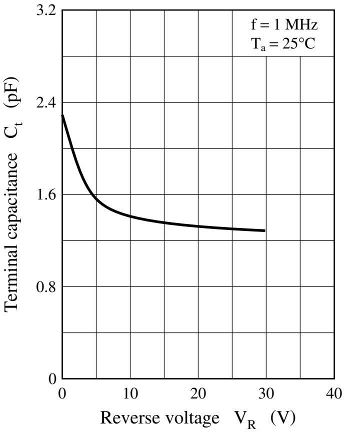
r_f — f



r_f — f



r_f — I_F



C_t — V_R